

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (High speed U-MOSIII)

TPC8010-H

DC-DC Converters
 Notebook PC Applications
 Portable Equipment Applications

- Small footprint due to small and thin package
- High speed switching
- Small gate charge: $Q_g = 18 \text{ nC}$ (typ.)
- Low drain-source ON resistance: $R_{DS(ON)} = 12 \text{ m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 11 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 10 \text{ }\mu\text{A}$ (max) ($V_{DS} = 30 \text{ V}$)
- Enhancement mode: $V_{th} = 1.1 \text{ to } 2.3 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

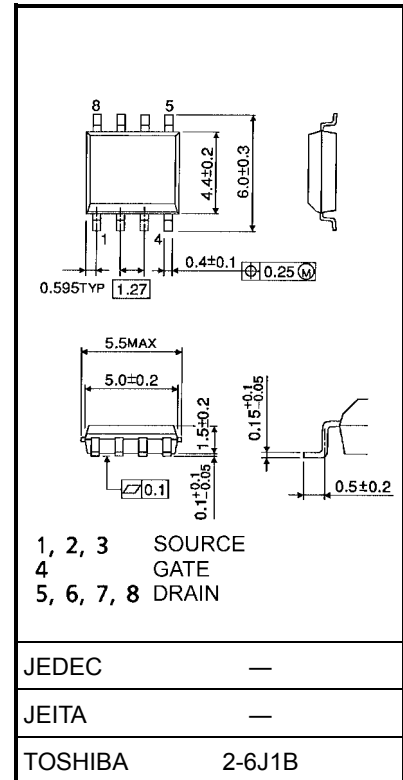
Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	30	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	11	A
	Pulse (Note 1)	I_{DP}	44	
Drain power dissipation ($t = 10 \text{ s}$) (Note 2a)		P_D	1.9	W
Drain power dissipation ($t = 10 \text{ s}$) (Note 2b)		P_D	1.0	W
Single pulse avalanche energy (Note 3)		E_{AS}	157	mJ
Avalanche current		I_{AR}	11	A
Repetitive avalanche energy (Note 2a) (Note 4)		E_{AR}	0.19	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Note: For (Note 1), (Note 2), (Note 3) and (Note 4), please refer to the next page.

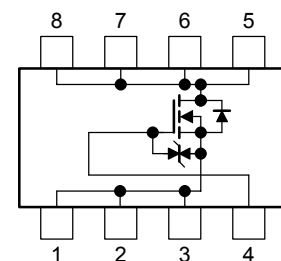
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 0.080 g (typ.)

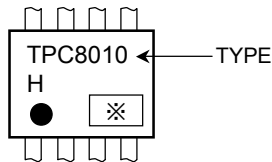
Circuit Configuration



Thermal Characteristics

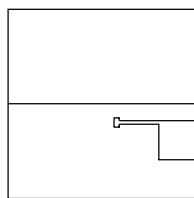
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th(ch-a)}$	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th(ch-a)}$	125	°C/W

Marking (Note 5)



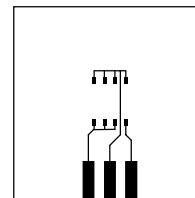
Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



(a)

FR-4
25.4 × 25.4 × 0.8
(unit: mm)



(b)

FR-4
25.4 × 25.4 × 0.8
(unit: mm)

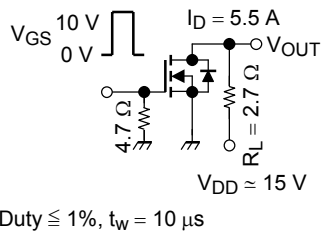
Note 3: $V_{DD} = 24\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 1.0\text{ mH}$, $R_G = 25\ \Omega$, $I_{AR} = 11\text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on lower left of the marking indicates Pin 1.

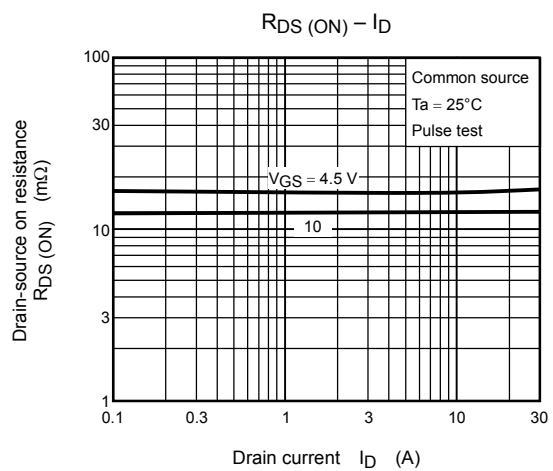
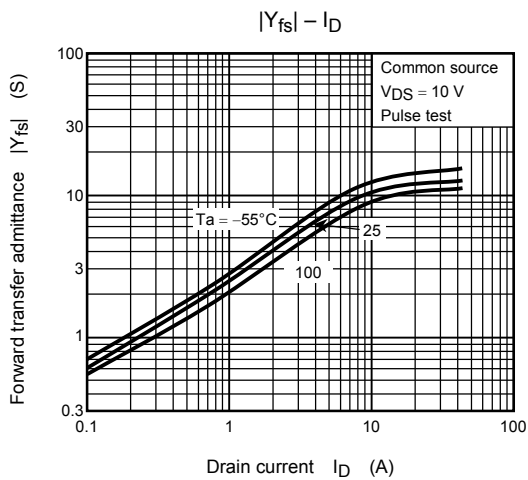
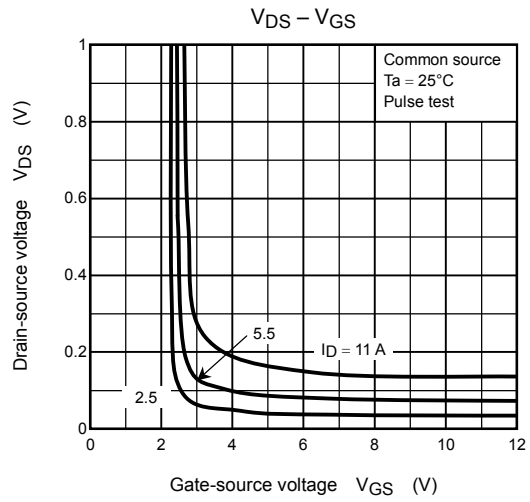
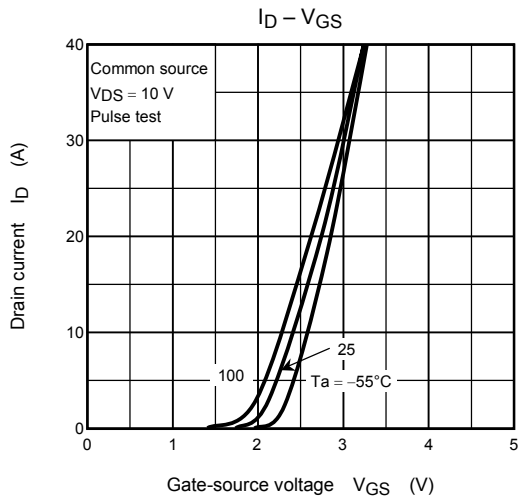
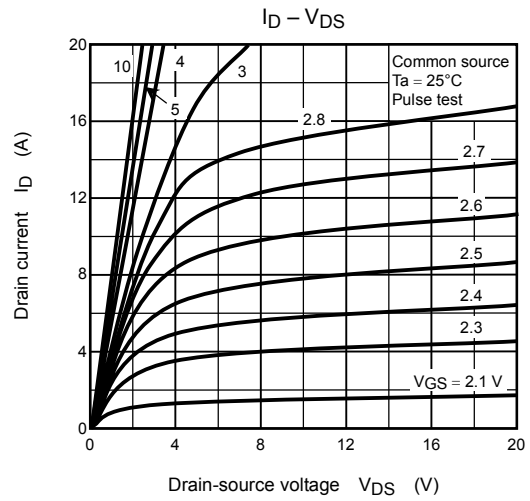
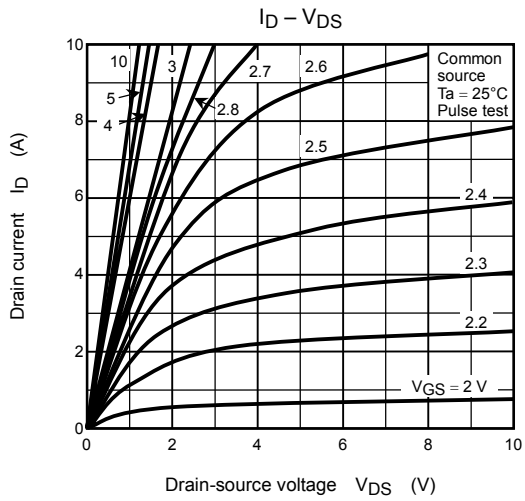
※ shows lot number. (year of manufacture: last decimal digit of the year of manufacture, month of manufacture: January to December are denoted by letters A to L respectively.)

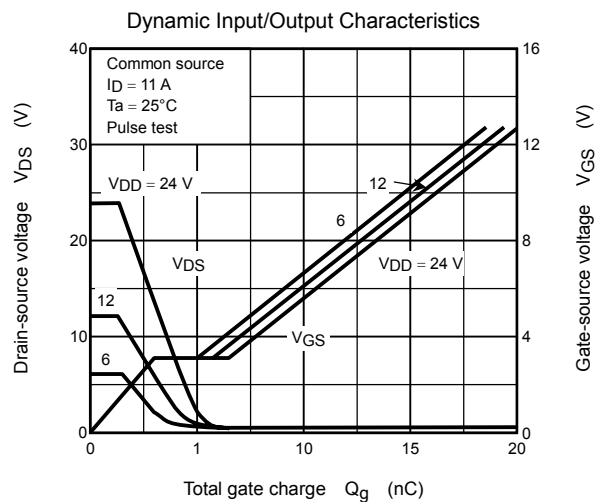
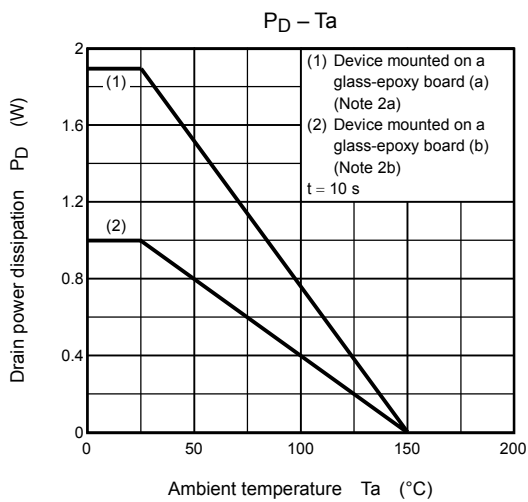
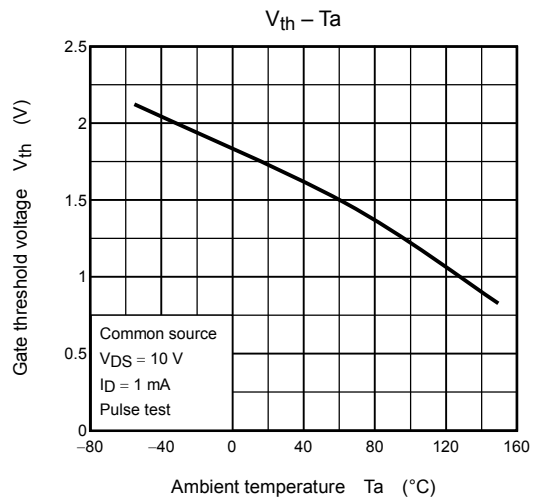
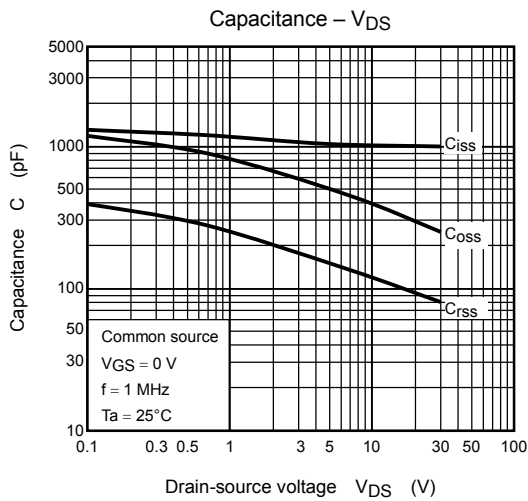
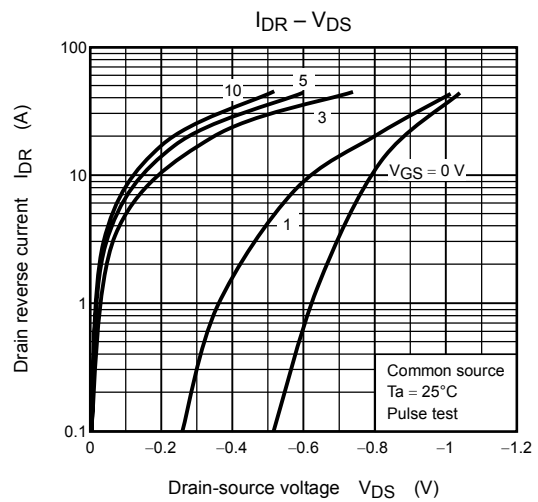
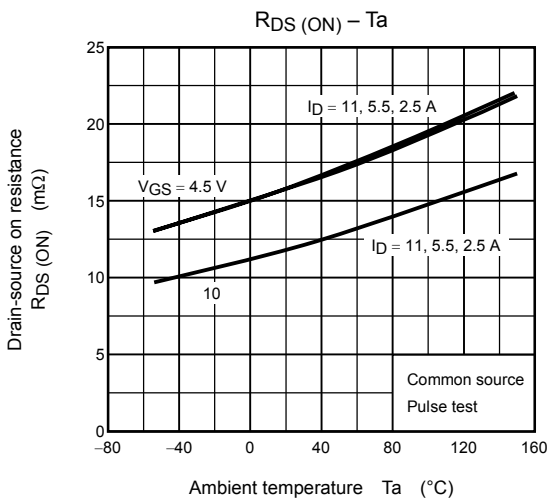
Electrical Characteristics (Ta = 25°C)

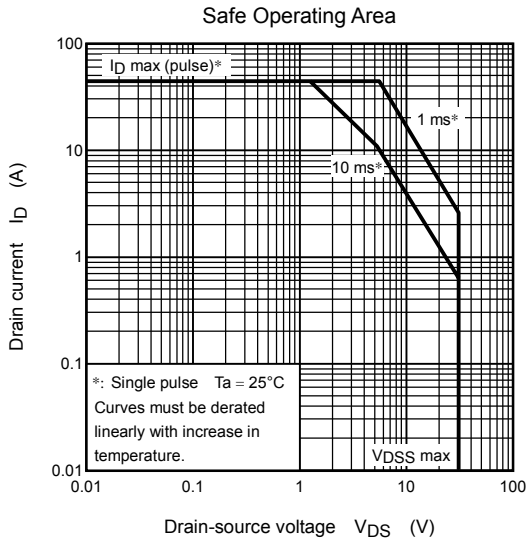
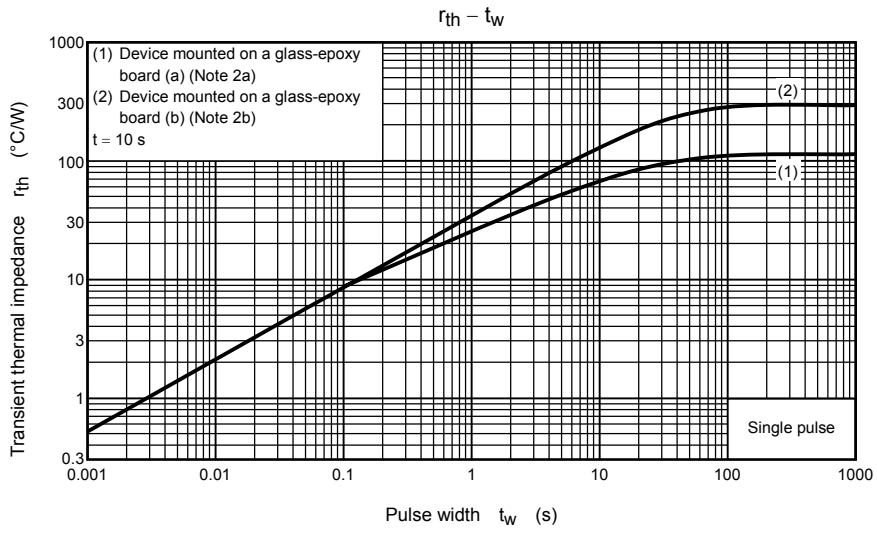
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain cut-OFF current		I_{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	10	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	—	—	V
		$V_{(BR)DSX}$	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	—	—	
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	1.1	—	2.3	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$	—	16	25	$\text{m}\Omega$
			$V_{GS} = 10 \text{ V}, I_D = 5.5 \text{ A}$	—	12	16	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 5.5 \text{ A}$	5.5	11	—	S
Input capacitance		C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	1020	—	pF
Reverse transfer capacitance		C_{rss}		—	120	—	
Output capacitance		C_{oss}		—	400	—	
Switching time	Rise time	t_r	 <p>$V_{GS} = 10 \text{ V}, 0 \text{ V}$ $I_D = 5.5 \text{ A}$ V_{OUT} $R_L = 2.7 \Omega$ $V_{DD} \approx 15 \text{ V}$ 4.7Ω Duty $\leq 1\%$, $t_w = 10 \mu\text{s}$</p>	—	3.1	—	ns
	Turn-ON time	t_{on}		—	11	—	
	Fall time	t_f		—	3.4	—	
	Turn-OFF time	t_{off}		—	23	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 11 \text{ A}$	—	18	—	nC
			$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 11 \text{ A}$	—	10	—	
Gate-source charge 1		Q_{gs1}		—	2.6	—	
Gate-drain ("miller") charge		Q_{gd}	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 11 \text{ A}$	—	4.4	—	
Gate switch charge		Q_{sw}		—	5.5	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	44	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = 11 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	-1.2	V







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